

DATA SHEET

TN6Q03 — Quasi-Resonant Switching Power Supply ExPD

Features

- Quasi-resonant type original control IC.
- High voltage power MOSFET with current sense.
- · Low input voltage protection (self reset)
- Overvoltage protection (latch).
- · Overcurrent protection (pulse-by-pulse).

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	unit				
[All voltage parameters are absolute voltage referenced to GND]								
Drain-to-Source Voltage	VDSS	3-5		V				
Drain Current (DC)	ID	3-5	4.5	А				
Drain Current (Pulse)	IDP	3-5 PW≤10µs, duty cycle≤1%	13.5	А				
VDD Pin Applied Voltage	VDD	4-5	-0.3 to 16.7	V				
FB Pin Applied Voltage	VFB	1-5	-0.3 to VDD+0.3	V				
EDGE Pin Applied Voltage	VEDGE	2-5	-0.3 to VDD+0.3	V				
Allowable Power Dissipation	PD		2	W				
		Tc=25°C	30	W				
Operating Temperature	Topr		-25 to +125	°C				
Junction Temperature	Tj		150	°C				
Storage Temperature	Tstg		-55 to +150	°C				
Avalanche Energy (Single Pulse) *1	EAS	3-5	105	mJ				
Avalanche Current *2	IAV	3-5	4.5	А				

*1 VDD=50V, L=10mH, IAV=4.5A

*2 L≤10mH, single pulse

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Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit		
Falametei		Conditions	min	typ	max	Onit		
[MOSFET]								
Drain-to-Source Breakdown Voltage	V(BR)DSS	3-5 I _D =1mA, V _{DD} =0	650			V		
Zero-Gate Voltage Drain Current	IDSS	3-5 VDS=650V, VDD=0			1	mA		
Static Drain-to-Source On-State Resistance	RDS(on)	3-5 ID=2.3A, VDD=15V		1.55	2.0	Ω		
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		1150		pF		
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		200		pF		
[IC]								
Power Supply Line Breakdown Voltage	V(BR)DD	4-5 IDD=1mA, VFB=0	16.7			V		
Overvoltage Input Latch Shutdown Threshold Voltage	OVP	4-5	15.7	16.5	17.3	V		
Burst Mode Start Threshold Voltage	VBon	4-5 VEDGE=VDD	15.2	16.0	16.8	V		
Burst Mode Stop Threshold Voltage	VBoff	4-5 VEDGE=VDD	14.6	15.4	16.2	V		
Burst Mode Hysteresis Voltage	ΔVB	4-5 VEDGE=VDD		0.6		V		
Low Voltage Protection Release Threshold Voltage	UVH	4-5	9.1	9.9	10.7	V		
Low Voltage Protection Operation Threshold Voltage	111/1	4.5	8.0	8.8	9.6	V		
(Latch Reset Threshold Voltage)	0vL	4-5						
Low Voltage Protection Hysteresis Voltage	ΔUV	4-5		1.1		V		
Feedback Detection Threshold Voltage	VFB	1-5	0.58	0.70	0.82	V		
Edge Signal Release Threshold Voltage	VEDGE-H	2-5	2.3	2.6	2.9	V		
Edge Signal Detection Threshold Voltage	VEDGE-L	2-5	1.6	1.9	2.2	V		
Edge Signal Hysteresis Voltage	∆VEDGE	2-5		0.7		V		
Reference Oscillation Frequency	fosc	3-5 VEDGE=0	30	35	40	kHz		
Maximum Oscillation Frequency	fmax	3-5	150	180	210	kHz		
Power Supply Current (at start-up)	IDD(on)	4-5		200		μΑ		
Minimum ON Time	ton(min)	3-5		300		ns		
Step Drive Voltage	tstep	3-5		200		ns		
Step Drive Gate Voltage	VGstep	3-5		V _{DD} -5.7		V		

Package Dimensions

unit : mm

2249



Block Diagram



Pin Definitions and Functions

Pin No.	Symbol	Name	Function
1	FB	Overcurrent / feedback terminal	Overcurrent detection / voltage control input
2	EDGE	EDGE dtection terminal	Delay EDGE voltage input
3	DRAIN	DRAIN terminal	Power MOSFET drain
4	VDD	Power supply terminal	Input for start-up voltage and drive voltage
5	SOURCE (GND)	Source (Ground) terminal	Power MOSFET source (ground)

Sample Application Circuit





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